

IN THE CLAIMS:

Listing of claims:

1. (currently amended)      A method for forming a head suspension assembly,  
comprising:  
    forming a trench extending into a substrate;  
    forming a sacrificial layer in ~~or on a portion of a substrate~~ the trench;  
    forming a ~~transfer~~ film across the substrate;  
    patterning a photoresist layer on top of the ~~transfer~~ film;  
    transferring ~~the an~~ image of the patterned photoresist layer through the ~~transfer~~ film;  
    removing the patterned photoresist layer; and  
    removing the sacrificial layer from the trench to form a cavity extending a distance into  
the substrate.
2. (currently amended)      A method as in claim 1, wherein the ~~transfer~~ film includes  
silicon.
3. (currently amended)      A method as in claim 1, wherein the transferring the image  
of the patterned photoresist layer through the ~~transfer~~ film is done using reactive ion etching.
4. (original)      A method as in claim 1, wherein the substrate comprises silicon and the  
sacrificial layer is formed by etching a trench in the substrate and filling the trench with a metal.
5. (original)      A method as in claim 4, wherein removing the sacrificial layer comprises  
etching the metal from the trench.
6. (currently amended)      A method as in claim 1, further comprising forming the  
~~transfer~~ film from a polymer material.

7. (currently amended) A method as in claim 1, wherein the substrate comprises silicon and the ~~transfer~~ film comprises polysilsesquioxone.

8. (currently amended) A method as in claim 1, wherein the cavity extends a width that is no greater than that of the substrate ~~suspension arm~~ and the cavity extends a depth that is less than ~~the~~ a depth of the substrate. ~~suspension arm~~.

9. (currently amended) A method as in claim 1, further comprising forming an adhesion layer between the substrate and the ~~transfer~~ film.

10. (currently amended) A method as in claim 3, wherein the ~~transfer~~ film comprises a resin, and positioning a slider on the resin after the removing the sacrificial layer.

11. (currently amended) A method for forming a head suspension assembly, comprising:

forming a polysilsesquioxone layer over a portion of a substrate;

forming a photoresist layer on the polysilsesquioxone layer;

patterning the photoresist layer; ~~and~~

etching the polysilsesquioxone layer using the patterned photoresist layer as a mask; and removing the patterned photoresist layer.

12. (original) A method as in claim 11, further comprising, prior to forming the photoresist layer, curing the polysilsesquioxone layer.

13. (original) A method as in claim 12, further comprising, prior to forming the polysilsesquioxone layer, forming a trench in the substrate and forming a sacrificial layer in the trench, wherein the polysilsesquioxone layer is formed over the sacrificial layer.

14. (original) A method as in claim 13, further comprising forming the sacrificial layer from a metal material.

15. (original) A method as in claim 13, further comprising forming the sacrificial layer from copper.

16. (original) A method as in claim 13, further comprising removing the sacrificial material from the trench after the etching the polysilsesquioxone layer.

17. (original) A method as in claim 12, further comprising positioning a slider on the cured polysilsesquioxone layer after the removing the patterned photoresist layer.

18. (new) A method for forming a head suspension assembly, comprising:  
forming a sacrificial material on a substrate;  
forming a layer on the substrate, wherein the sacrificial layer is positioned between a portion of the substrate and a portion of the film;  
forming a patterned photoresist on the layer;  
etching the layer using the patterned photoresist as a mask;  
removing the patterned photoresist after the etching;  
removing the sacrificial material after the removing the patterned photoresist layer; and  
positioning a slider on the etched layer.

19. (new) A method as in claim 18, wherein the layer comprises a polysilsesquioxone material.

20. (new) A method as in claim 18, further comprising forming a trench in the substrate and forming the sacrificial material in the trench.